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Appl. No. 09/639,635 Amdt. Dated 5 December 2003 Reply to Office action of 10 October 2003

I hereby certify that this correspondence is being facelmile transmitted to the Central Facsimile Number (703) 872-9306 of the United States Patent and Trademark Office on 5 December 2003 (Date). (4 pages total) on 5 December 2005 to Land M. Agosti.
Typed or printed name: Ann M. Agosti. Signature: ___C__

Appl. No.

09/639,636

Applicant

Guida et al.

Filed Title

High Resolution Anti-Scatter X-ray Grid and Laser Fabrication Method

TC/A.U. Examiner 1722 Luk, Emmanuel S.

Docket No.

RD25905-6

Customer No.

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Mail Stop AF Commissioner for Patents P.O. Box 1450 Alexandria, VA 22313-1450

RESPONSE UNDER 37 CFR 1,116

This case has been carefully reviewed in light of the Final Office Action dated 10 October 2003, wherein claims 10-11 and 15-17 were rejected under 35 USC 103(a) on Lembda Physik Industrial Report; claim 12 was rejected under 95 USC 103(a) on Lambda Physik Industrial Report in view of Konishi, US Patent No. 6,034,825; and claims 18-21 were rejected under 35 USC 103(a) on Lambda Physick Industrial Report in view of Guida et

Claims 10-12 and 15-21 remain pending in this application. Reconsideration in light of the following al., US Patent No. 5,557,650. remarks is respectfully requested.

Applicants respectfully traverse the rejection of claims 10-11 and 15-17 under 35 USC 103(a) over Lambda Physik Industrial Report. Applicants respectfully submit that Lambda does not teach or disclose the claim 10 recitations of (with emphasis added):

Claim 10 (previously presented). A system for patterning a substantially transparent polymer substrate of an anti-scatter x-ray grid, the system comprising:

a high power laser for providing laser light;

a beam homogenizer for conditioning the laser light; and

a phase mask for creating a pattern of the conditioned laser light while reducing an amount of the

the laser, the beam homogenizer, and the phase mask being positioned for ablating openings having slopes less than or equal to 0.25 degrees and extending completely through an anti-scatt r x-ray grid substrate having a thickness ranging from 0.3 millimeters to 1.5 millimeters.

Neither of the Lambda reference examples relate to x-ray grid substrates. One example relates to via formation (pages 1-6), and the other relates to ink jet nozzles (pages 6-8).

Pages 1-6 of the Lambda reference describes conventional via formation for electronic packaging applications with wall angle ranges described as 50-65 degrees for 1987 and 20-75 degrees for 1994 (page 3, table 2) and shows wall angles in FIGs. 10 and 11 that are necessary for metal coverage (bottom left of page 5).

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